

Features

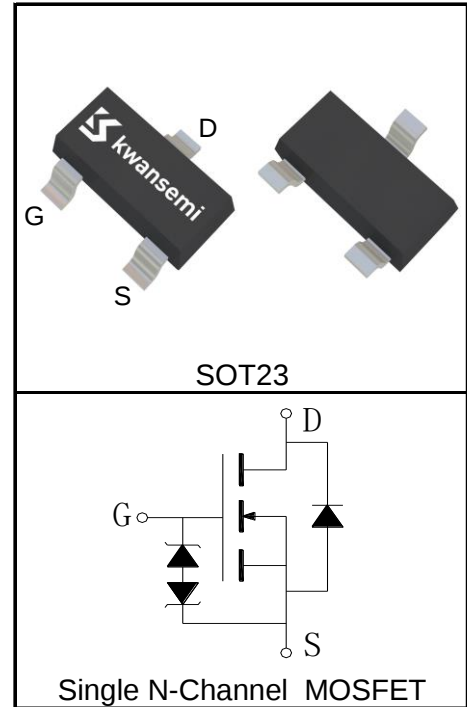
- 60V/0.3A,
 $R_{DS(ON)} = 1.8\Omega(\text{Typ.})@V_{GS}=10V$
 $R_{DS(ON)} = 1.9\Omega(\text{Typ.})@V_{GS}=4.5V$
- Low $R_{DS(ON)}$
- Super High Dense Cell Design
- Reliable and Rugged
- ESD Protected (HBM>2000V)

Applications

- Load Switch



Pin Description



Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _A =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		60	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _J ,T _{STG}	Operating and Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current	T _A =25°C	0.3	A
Mounted on Large Heat Sink				
I _{DP} ^①	Pulse Drain Current	T _A =25°C	1.2	A
I _D ^②	Continuous Drain Current(V _{GS} =10V)	T _A =25°C	0.3	A
		T _A =70°C	0.24	
P _D	Maximum Power Dissipation	T _A =25°C	0.5	W
		T _A =70°C	0.32	
R _{θJL}	Thermal Resistance-Junction to Lead		80	°C/W
R _{θJA} ^③	Thermal Resistance-Junction to Ambient		250	°C/W
Drain-Source Avalanche Ratings				
E _{AS} ^④	Avalanche Energy, Single Pulsed		0.2	mJ

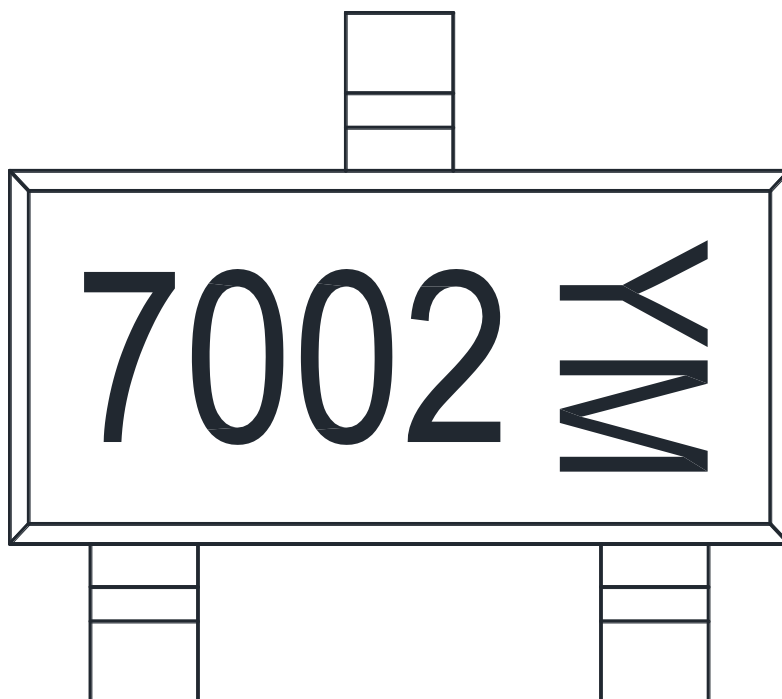
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	Rating			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V			1	μA
		T _J =125°C			30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.1	1.6	2.1	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V			±10	μA
R _{DS(ON)} ⑤	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =0.5A		1.8	3	Ω
		V _{GS} =4.5V, I _{DS} =0.3A		1.9	4	Ω
Diode Characteristics						
V _{SD} ⑤	Diode Forward Voltage	I _{SD} =0.5A, V _{GS} =0V		0.91	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =0.5A, dI _{SD} /dt=100A/μs		14		ns
Q _{rr}	Reverse Recovery Charge			11		nC
Dynamic Characteristics ⑥						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		140		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, Frequency=1.0MHz		21		pF
C _{oss}	Output Capacitance			4		
C _{rss}	Reverse Transfer Capacitance			2		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V, I _{DS} =0.5A, V _{GEN} =10V, R _G =6Ω		5		ns
t _r	Turn-on Rise Time			6		
t _{d(OFF)}	Turn-off Delay Time			11		
t _f	Turn-off Fall Time			3		
Gate Charge Characteristics ⑥						
Q _g	Total Gate Charge	V _{DS} =30V, V _{GS} =10V, I _{DS} =0.5A		1.3		nC
Q _{gs}	Gate-Source Charge			0.3		
Q _{gd}	Gate-Drain Charge			0.3		

- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature.
 - ③ When mounted on 1 inch square copper board, $t \leq 10\text{sec}$. The value in any given application depends on the user's specific board design.
 - ④ Limited by T_{Jmax} , Starting $T_J = 25^{\circ}\text{C}$, $I_{ASmax} = 2A$, $L = 0.1\text{mH}$, $V_{DD} = 48V$, $R_G = 25\Omega$, $V_{GS} = 10V$. Part not recommended for use above this value.
 - ⑤ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑥ Guaranteed by design, not subject to production testing.

Ordering and Marking Information

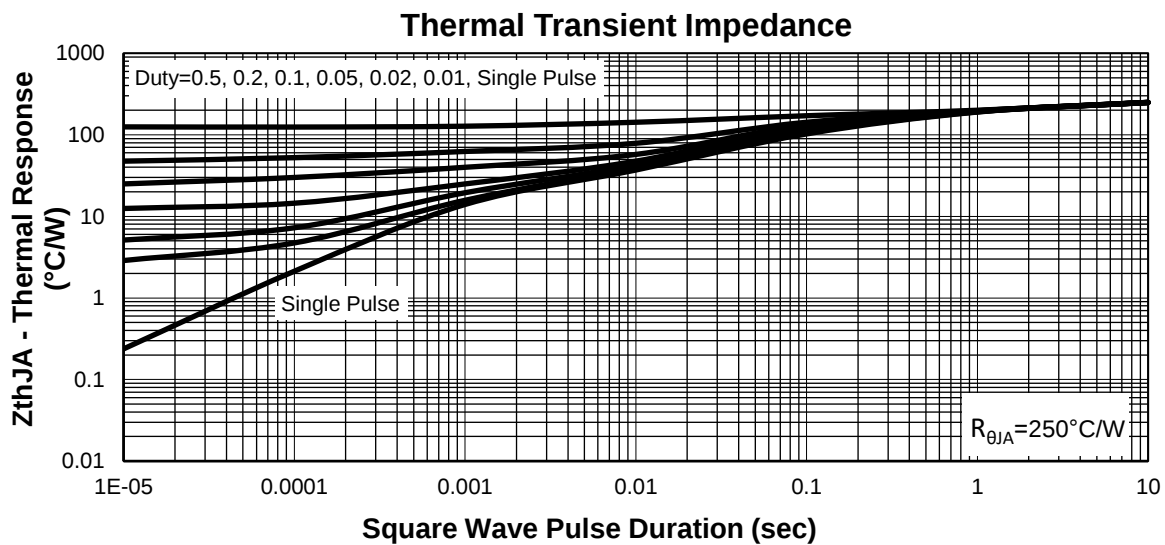
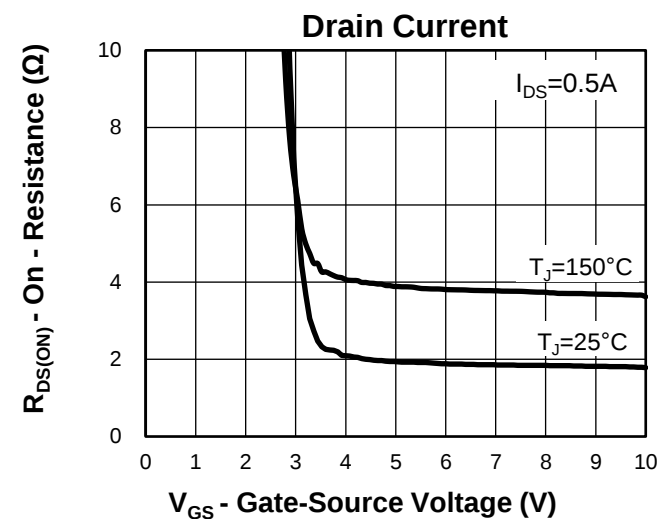
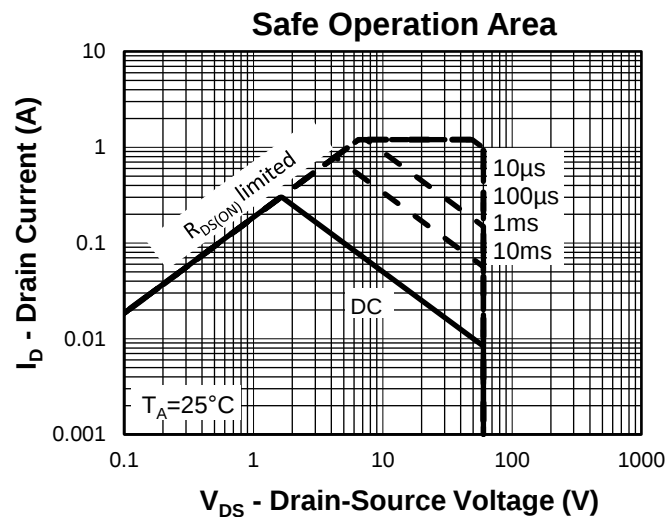
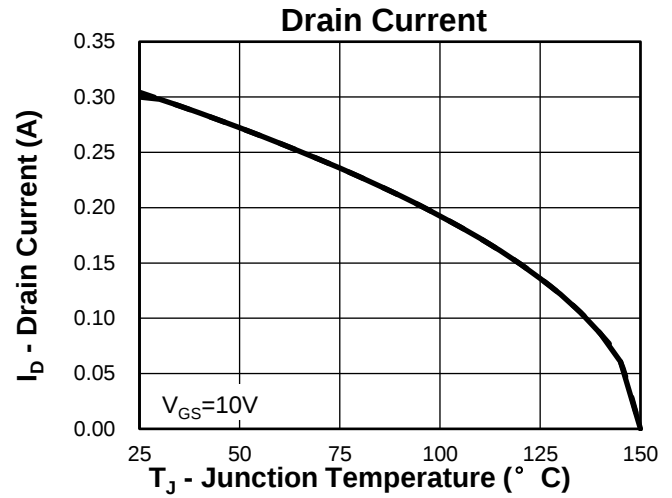
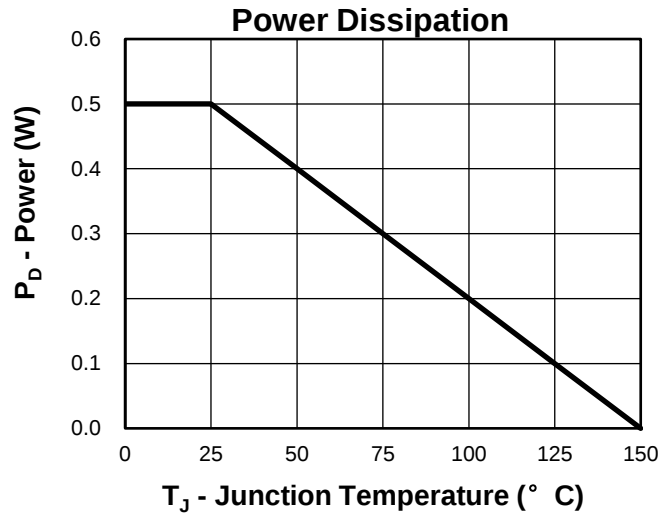
Device	Package	Packaging	Quantity	Reel Size	Tape width
KS2N7002AA	SOT23	Tape&Reel	3000	7"	8mm



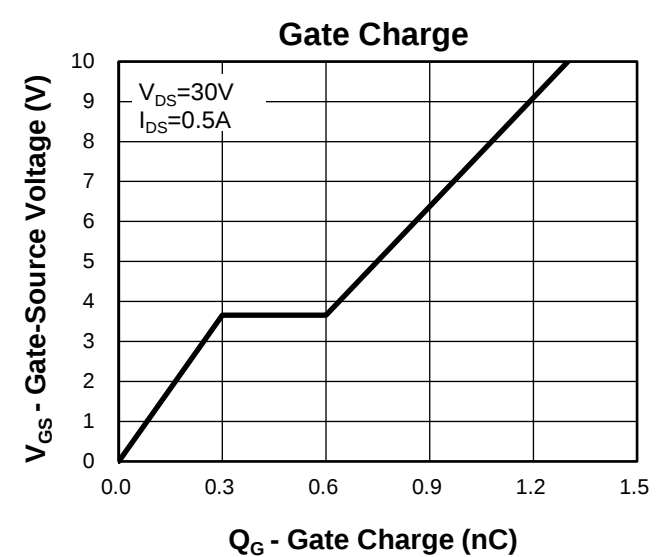
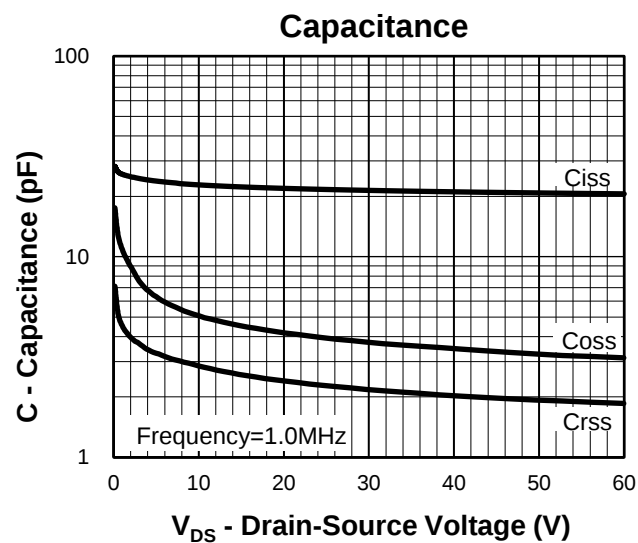
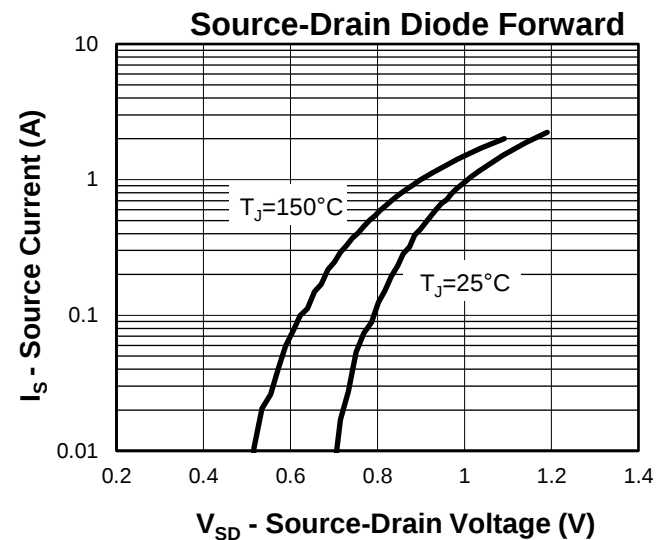
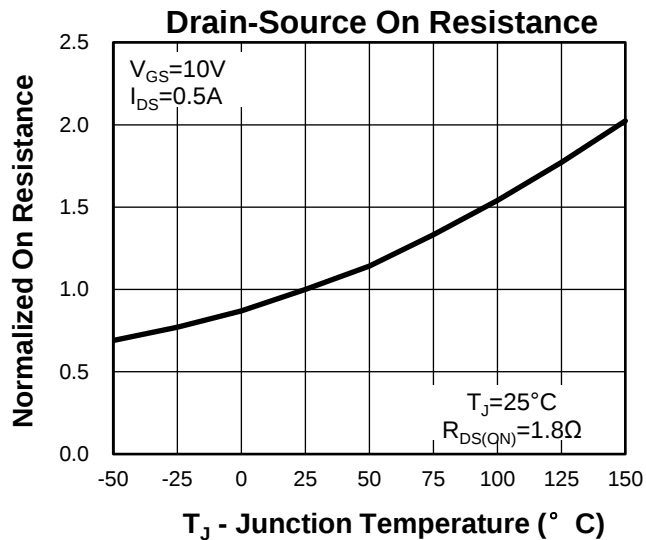
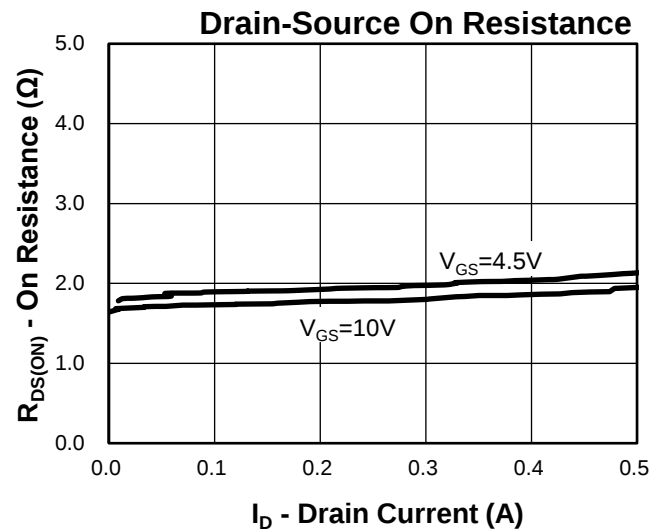
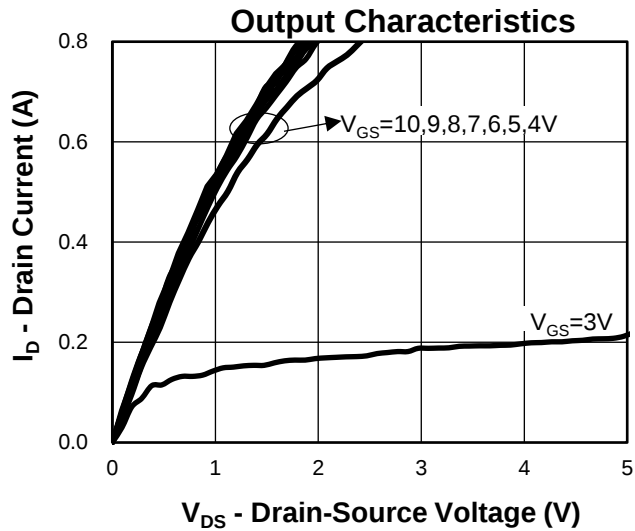
Y =Year,2017-A,2018-B,etc.

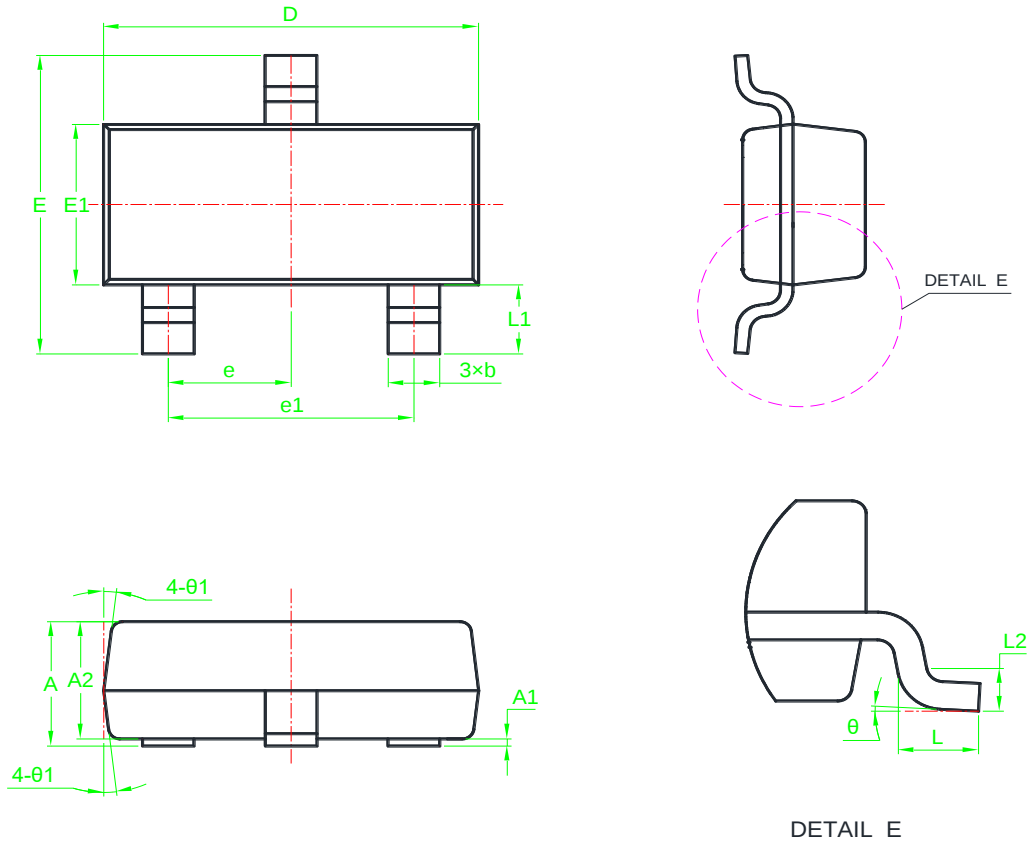
M =Month,Jan-1,Feb-2,....Sep-9,Oct-A,Nov-B,Dec-C.

Typical Characteristics



Typical Characteristics



Package Information
SOT23


SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	*	1.12	0.035	*	0.044	e	0.95BSC			0.037BSC		
A1	0.01	*	0.10	0.000	*	0.004	e1	1.90BSC			0.075BSC		
A2	0.80	0.90	1.02	0.031	0.035	0.040	L	0.30	0.40	0.50	0.012	0.016	0.020
b	0.30	0.40	0.50	0.012	0.016	0.020	L1	0.54REF			0.021REF		
D	2.80	2.90	3.00	0.110	0.114	0.118	L2	0.254BSC			0.010BSC		
E	2.25	2.40	2.55	0.089	0.094	0.100	θ	0°	*	8°	0°	*	8°
E1	1.20	1.30	1.40	0.047	0.051	0.055	θ 1	0°	*	10°	0°	*	10°

Note: Dimensions do not inclusive burrs and mold flash.

Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



Diode Recovery Test Circuit and Waveforms



Gate Charge Test Circuit and Waveform



Customer Service

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